Product data sheet

1. General description

Hyperfast power diode in a SOD113A package.

2. Features and benefits

- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Half-bridge/full-bridge switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _h ≤ 97 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		-	-	5	А
Static characte	eristics						
V _F	forward voltage	I _F = 5 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.35	2.1	V
Dynamic chara	Dynamic characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	11	-	ns





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113A)	

6. Ordering information

Table 3. Ordering information

Tuble 6. Ordering mornidation						
Type number	Package					
	Name	Description	Version			
BYC5X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220F "full pack"	SOD113A			

7. Marking

Table 4. Marking codes

Type number	Marking code
BYC5X-600P	BYC5X-600P

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _h ≤ 97 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	5	A
I _{FRM}	repetitive peak forward current	\bar{o} = 0.5; t _p = 25 μs; T _h ≤ 97 °C; squarewave pulse	-	10	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	60	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	65	A
T _{stg}	storage temperature		-65	175	°C
T _j	junction temperature		-	175	°C

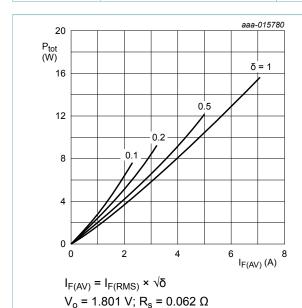
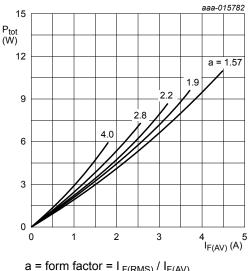


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = I $_{F(RMS)}$ / $I_{F(AV)}$ V_o = 1.801 V; R_s = 0.062 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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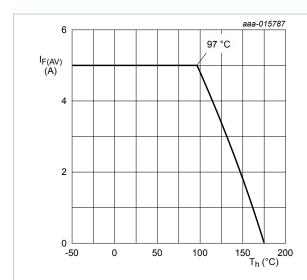


Fig. 3. Forward current as a function of heatsink temperature; maximum values

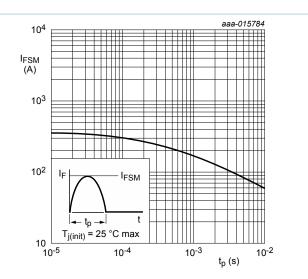


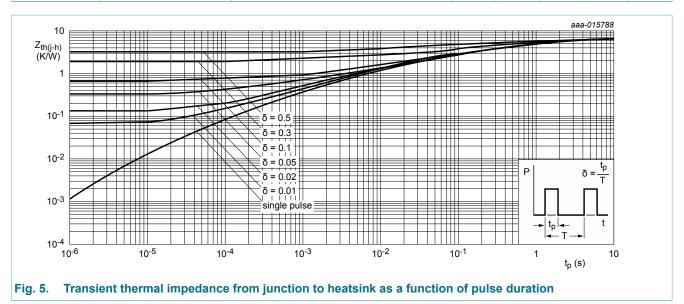
Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

Hyperfast power diode

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; Fig. 5	-	-	6.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



10. Isolation characteristics

Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF

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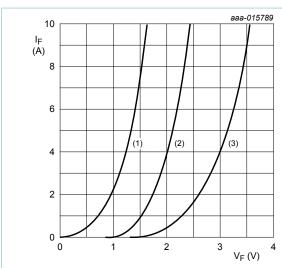
Hyperfast power diode

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics			'		
V _F	forward voltage	I _F = 5 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.5	3.3	V
		I _F = 5 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.35	2.1	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	0.6	mA
Dynamic cl	naracteristics		'			
Q _r rec	recovered charge	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	19	-	nC
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	45	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	11	-	ns
		I _F = 5 A; V _R = 200 V; dI _F /dt = 200 A/µs;	-	23	-	ns
		T _j = 25 °C; <u>Fig. 7</u>	-	28	-	ns
		$I_F = 5 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	13	25	ns
I _{RM}	peak reverse recovery current	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	1.7	-	Α
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	3.2	-	Α

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 V_o = 1.833 V; R_s = 0.055 Ω

(1) T_j = 150 °C; typical values

(2) T_j = 150 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

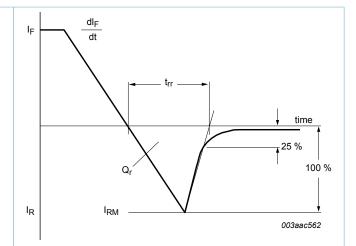


Fig. 7. Reverse recovery definitions; ramp recovery

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12. Package outline

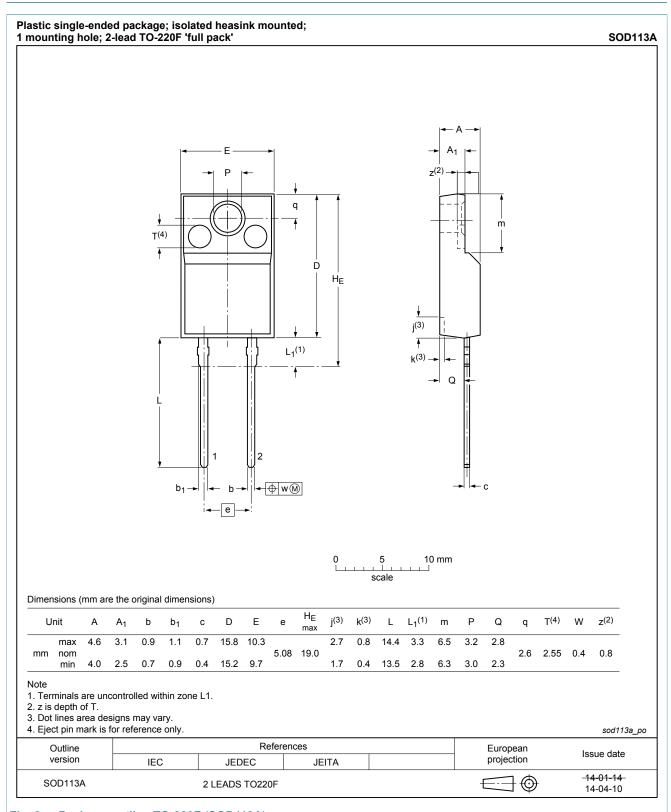


Fig. 8. Package outline TO-220F (SOD113A)

BYC5X-600P

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